Erratum: Rocking curve peak shift in thin semiconductor layers
[J. Appl. Phys. 66, 985 (1989)]

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The statement "a wrong boundary condition, saying that the amplitude X is zero deep inside the substrate crystal" on page 986 is incorrect. In fact, our boundary condition Eq. (2) can be obtained from Halliwel's analytical formula for a single-crystal layer by setting X = 0 at the back side of the crystal layer and assuming the layer thickness to be infinite in her formula. Therefore, our Eq. (2) and the above boundary condition yield the same result. The above statement, however, does not affect any other contents and conclusions of our paper.


Erratum: Dynamical x-ray diffraction from nonuniform crystalline films: Application to x-ray rocking curve analysis [J. Appl. Phys. 59, 3743 (1986)]

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The expression for A, on page 3744, should have been:

\[ A = \pi z \left| \psi_{B}^{0} \right| / \lambda \sqrt{\gamma_{F} \gamma_{H}} \]

and the expressions for \( c_1 \) and \( c_2 \) should have been:

\[ c_1 = 2 \sin(2\Theta_B) \left[ \cos^2 \varphi \tan \Theta_B \pm \sin \varphi \cos \varphi \right] \]

and

\[ c_2 = 2 \sin(2\Theta_B) \left[ \sin^2 \varphi \tan \Theta_B \mp \sin \varphi \cos \varphi \right] \]

respectively.